NSN 5961-00-892-0988

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-892-0988 **Inclosure Material:** Metal **Overall Length:** Between 0.240 inches and 0.260 inches **Overall Diameter:** Between 0.335 inches and 0.370 inches **Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method: Terminal Terminal Circle Diameter:** 0.200 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 3.0 gate trigger voltage, dc and 2.0 on-state voltage, dc **Current Rating Per Characteristic:** 1.00 amperes forward current, total rms nanoamperes and 10.00 milliamperes forward current, total rms preset **Maximum Operating Tempurature Per Measurement Point:** 80.0 degrees celsius case **Special Features:** Junction pattern arrangement: pnpn **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: